

Silicon Controlled Rectifiers

Reverse Blocking Triode Thyristors

... designed for industrial and consumer applications such as power supplies; battery chargers; temperature, motor, light and welder controls.

- Economical for a Wide Range of Uses
- High Surge Current — $I_{TSM} = 350$ Amp
- Practical Level Triggering and Holding Characteristics —
 4 and 5.2 mA (Typ) @ $T_C = 25^\circ\text{C}$
- Rugged Construction in Either Pressfit, Stud or Isolated Stud Package

**2N3870
 thru
 2N3873
 2N3896
 thru
 2N3899
 2N6171
 thru
 2N6174**

**SCRs
 35 AMPERES RMS
 100 thru 800 VOLTS**

MAXIMUM RATINGS ($T_C = 100^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
*Peak Repetitive Forward or Reverse Blocking Voltage, Note 1 ($T_J = -40$ to $+100^\circ\text{C}$, 1/2 Sine Wave, 50 to 400 Hz, Gate Open) 2N3870, 2N3896, 2N6171 2N3871, 2N3897, 2N6172 2N3872, 2N3898, 2N6173 2N3873, 2N3899, 2N6174	V_{RRM} or V_{DRM}	100 200 400 600	Volts
*Peak Non-Repetitive Forward or Reverse Blocking Voltage ($t \leq 5$ ms) 2N3870, 2N3896, 2N6171 2N3871, 2N3897, 2N6172 2N3872, 2N3898, 2N6173 2N3873, 2N3899, 2N6174	V_{RSM} or V_{DSM}	150 330 660 700	Volts
*Average On-State Current, Note 2 ($T_C = -40$ to $+65^\circ\text{C}$) ($T_C = +85^\circ\text{C}$)	$I_T(AV)$	22 11	Amps
*Peak Non-Repetitive Surge Current (One cycle, 60 Hz) ($T_C = +65^\circ\text{C}$)	I_{TSM}	350	Amps
Circuit Fusing ($T_C = -40$ to $+100^\circ\text{C}$) ($t = 1$ to 8.30 ms)	I^2t	510	A^2s

* Indicates JEDEC Registered Data.

Notes: 1. Ratings apply for zero or negative gate voltage. Devices shall not have a positive bias applied to the gate concurrently with a negative potential on the anode. Devices should not be tested with a constant current source for forward or reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

2. Isolated stud devices must be derated an additional 10 percent.



(TO-209)

2N3870 thru 2N3873



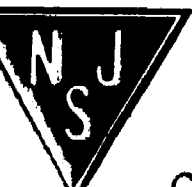
CASE 175-03

2N3896 thru 2N3899



CASE 311-02

(Stud Isolated)
 2N6171 thru 2N6174



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2N3870 thru 2N3873 • 2N3896 thru 2N3899 • 2N6171 thru 2N6174

MAXIMUM RATINGS (T_C = 100°C unless otherwise noted.)

Rating	Symbol	Value	Unit
*Peak Gate Power	PGM	20	Watts
*Average Gate Power	PG(AV)	0.5	Watt
*Peak Forward Gate Current	I _{GM}	2	Amps
Peak Gate Voltage	V _{GM}	10	Volts
*Operating Junction Temperature Range	T _J	-40 to +100	°C
*Storage Temperature Range	T _{stg}	-40 to +150	°C
Stud Torque	—	30	in. lb.

*Indicates JEDEC Registered Data.

***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case 2N3870 thru 2N3873, 2N3896 thru 2N3899 2N6171 thru 2N6174	R _{θJC}	0.9 1	°C/W

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max*	Unit
*Peak Forward or Reverse Blocking Current (Rated V _{DRM} or V _{RRM} , gate open, T _J = 100°C) 2N3870, 2N3896, 2N6171 2N3871, 2N3897, 2N6172 2N3872, 2N3898, 2N6173 2N3873, 2N3899, 2N6174 (Rated V _{DRM} or V _{RRM} , gate open, T _J = 25°C) All Devices	I _{DRM} , I _{RRM}	— — — — —	1 1 1 1 —	2 2.5 3 4 10	mA μA
*Peak On-State Voltage (I _{TM} = 69 A Peak)	V _{TM}	—	1.5	1.85	Volts
*Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 24 ohms)	I _{GT}	— —	9 4	80 40	mA
*Gate Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 24 ohms)	V _{GT}	— —	0.9 0.69	3 1.6	Volts
*Holding Current (Gate Open) (V _D = 12 V, I _{TM} = 200 mA)	I _H	— —	14 6.2	90 50	mA
*Gate Controlled Turn-On Time (t _d + t _r) (I _{TM} = 41 Adc, V _D = rated V _{DRM} , I _{GT} = 40 mAdc, Rise Time ≤ 0.05 μs, Pulse Width = 10 μs)	t _{gt}	—	—	1.5	μs
Circuit Commutated Turn-Off Time (I _{TM} = 10 A, I _R = 10 A) (I _{TM} = 10 A, I _R = 10 A, T _C = 100°C)	t _q	— —	25 35	— —	μs
Forward Voltage Application Rate (T _C = 100°C, V _D = Rated V _{DRM})	dv/dt	—	50	—	V/μs